Low-Voltage CMOS Quad 2-Input NAND Gate With 5V-Tolerant Inputs

The MC74LCX00 is a high performance, quad 2–input NAND gate operating from a 2.3 to 3.6V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5V allows MC74LCX00 inputs to be safely driven from 5V devices.

Current drive capability is 24mA at the outputs.

- Designed for 2.3 to 3.6V V_{CC} Operation
- 5V Tolerant Inputs Interface Capability With 5V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10µA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500mA
- ESD Performance: Human Body Model >2000V; Machine Model >200V

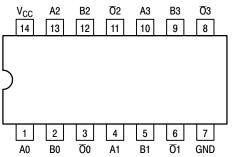


Figure 1. LOGIC DIAGRAM

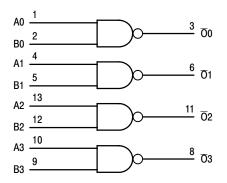
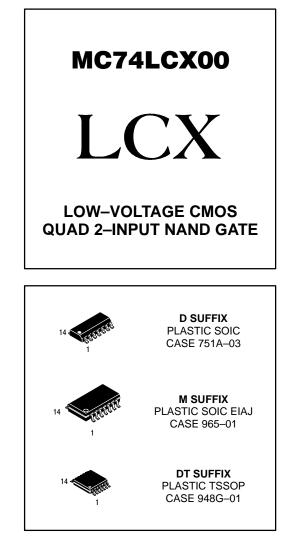


Figure 2. Pinout: 14-Lead (Top View)



PIN NAMES

Pins	Function
An, Bn	Data Inputs
O n	Outputs

FUNCTION TABLE

Inp	uts	Outputs
An	Bn	Ōn
L	L	Н
L	Н	Н
н	L	Н
н	Н	L

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1.	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	$V_{O} > V_{CC}$	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage (HIGH or LOW State)	0		V _{CC}	V
I _{OH}	HIGH Level Output Current, $V_{CC} = 3.0V - 3.6V$			-24	mA
I _{OL}	LOW Level Output Current, $V_{CC} = 3.0V - 3.6V$			24	mA
I _{OH}	HIGH Level Output Current, $V_{CC} = 2.7V - 3.0V$			-12	mA
I _{OL}	LOW Level Output Current, $V_{CC} = 2.7V - 3.0V$			12	mA
T _A	Operating Free–Air Temperature	-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V _{IN} from 0.8V to 2.0V, V _{CC} = $3.0V$	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C	C to +85°C	
Symbol	Characteristic	Condition	Min	Мах	Unit
V _{IH}	HIGH Level Input Voltage (Note 2.)	$2.7V \le V_{CC} \le 3.6V$	2.0		V
V _{IL}	LOW Level Input Voltage (Note 2.)	$2.7V \leq V_{CC} \leq 3.6V$		0.8	V
V _{OH}	HIGH Level Output Voltage	$2.7V \leq V_{CC} \leq 3.6V; \ I_{OH} = -100 \mu A$	V _{CC} - 0.2		V
		$V_{CC} = 2.7V; I_{OH} = -12mA$	2.2		1
		$V_{CC} = 3.0V; I_{OH} = -18mA$	2.4		
		$V_{CC} = 3.0V; I_{OH} = -24mA$	2.2		1
V _{OL}	LOW Level Output Voltage	$2.7V \le V_{CC} \le 3.6V; I_{OL} = 100 \mu A$		0.2	V
		V _{CC} = 2.7V; I _{OL} = 12mA		0.4	1
		V _{CC} = 3.0V; I _{OL} = 16mA		0.4	1
		V _{CC} = 3.0V; I _{OL} = 24mA		0.55]

2. These values of VI are used to test DC electrical characteristics only.

DC ELECTRICAL CHARACTERISTICS (continued)

			$T_A = -40^{\circ}C$ to +85°C		
Symbol	Characteristic	Condition	Min	Max	Unit
l _l	Input Leakage Current	$2.7 \text{V} \leq \text{V}_{CC} \leq 3.6 \text{V}; \ 0 \text{V} \leq \text{V}_{I} \leq 5.5 \text{V}$		±5.0	μA
I _{CC}	Quiescent Supply Current	$2.7 \leq V_{CC} \leq 3.6 \textrm{V}; ~\textrm{V}_{\textrm{I}} = \textrm{GND} ~\textrm{or} ~\textrm{V}_{CC}$		10	μA
		$2.7 \leq V_{CC} \leq 3.6 \text{V}; \ 3.6 \leq \text{V}_{\text{I}} \leq 5.5 \text{V}$		±10	μA
ΔI_{CC}	Increase in I _{CC} per Input	$2.7 \leq V_{CC} \leq 3.6 \textrm{V}; \ \textrm{V}_{IH} = \textrm{V}_{CC} - 0.6 \textrm{V}$		500	μA

AC CHARACTERISTICS ($t_R = t_F = 2.5ns$; $C_L = 50pF$; $R_L = 500\Omega$)

				Limits		
			TA	, = −40°C to +	⊦85°C	
			V _{CC} = 3.0	V to 3.6V	V _{CC} = 2.7V	
Symbol	Parameter	Waveform	Min	Мах	Мах	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	1.5 1.5	5.2 5.2	6.0 6.0	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3.)			1.0 1.0		ns

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

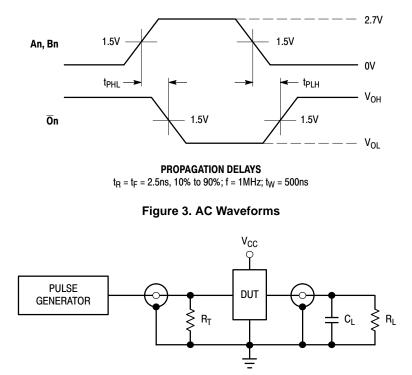
DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4.)	V_{CC} = 3.3V, C_{L} = 50pF, V_{IH} = 3.3V, V_{IL} = 0V		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4.)	V_{CC} = 3.3V, C_{L} = 50pF, V_{IH} = 3.3V, V_{IL} = 0V		0.8		V

4. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 3.3V, V_{I} = 0V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3V, V_{I} = 0V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10MHz, V_{CC} = 3.3V, V_{I} = 0V or V_{CC}	25	pF

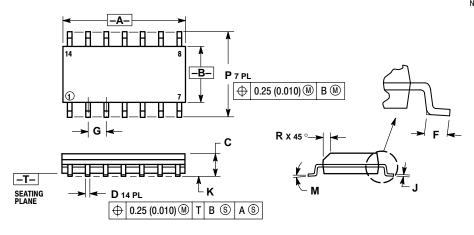


 $\begin{array}{l} C_L = 50 pF \mbox{ or equivalent (Includes jig and probe capacitance)} \\ R_L = R_1 = 500 \Omega \mbox{ or equivalent} \\ R_T = Z_{OUT} \mbox{ of pulse generator (typically 50 \Omega)} \end{array}$



OUTLINE DIMENSIONS

D SUFFIX PLASTIC SOIC PACKAGE CASE 751A-03 **ISSUE F**



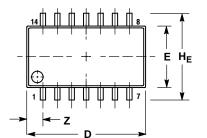
NOTES: DIES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

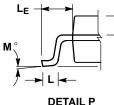
- 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

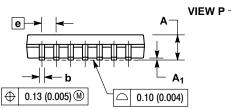
	MILLIMETERS INCHES			
	MILLINETERS			
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
Κ	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

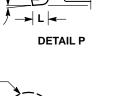
M SUFFIX PLASTIC SOIC EIAJ PACKAGE CASE 965-01 ISSUE O

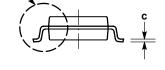
Q₁











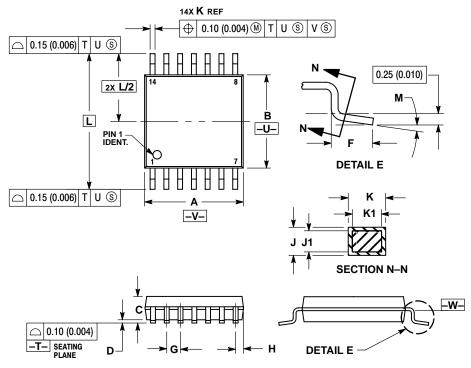
NOTES

- IDENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS OLUD FLASH OR
 - PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 4.
- PER SIDE. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH 5. DIMENSION AT MAXIMUM MATERIAL CONDITION. DIMENSION AT INFAMOLIN MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
М	0 °	10 °	0 °	10 °
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

OUTLINE DIMENSIONS

DT SUFFIX PLASTIC TSSOP PACKAGE CASE 948G-01 ISSUE O



NOTES:

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SNALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L		BSC	0.252 BSC	
Μ	0 °	8°	0°	8 °

<u>Notes</u>

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